

EAST - [09801990.wsp:1]

File View Edit Tools Window Help

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 (163) metal-ferroelectric-metal-insulator-se
 (163) metal-ferroelectric-metal-insulator-se
 (64) (metal-ferroelectric-metal-insulator-se
 (114) ("MFM" or metal-ferroelectric-metal
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DBs: USPAT, EPO, JPO, DERWENT, IBM, TDB

Plurals

Default operator: OR

Highlight all hit terms initially

(metal-ferroelectric-metal-insulator-semiconductor or (metal adj ferroelectric adj metal adj insulator adj semiconductor) or "MFMS") and (("MFM" or metal-ferroelectric-metal or (metal adj ferroelectric adj metal)) and ("MIS" or metal-insulator-semiconductor or (metal adj insulator adj semiconductor)))

ORSI ISAR Image Text HTML

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6649957 B2	20031118	7	Thin film polycrystalline memory structure	257/295	257/310; 257/E21.208
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6636435 B2	20031021	8	Ferroelectric memory cell array and method of storing data using the same	365/145	365/149
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6534326 B1	20030318	7	Method of minimizing leakage current and improving breakdown voltage of	438/3	257/E21.208; 438/240;
4	<input type="checkbox"/>	<input type="checkbox"/>	US 6509594 B2	20030121	6	Semiconductor memory device having MFMS transistor and increased data	257/295	257/315
5	<input type="checkbox"/>	<input type="checkbox"/>	US 6459110 B1	20021001	10	Semiconductor storage element	257/295	365/145; 365/182;
6	<input type="checkbox"/>	<input type="checkbox"/>	US 6449185 B2	20020910	23	Semiconductor memory and method for driving the same	365/145	365/189.09
7	<input type="checkbox"/>	<input type="checkbox"/>	US 6438021 B1	20020820	20	Methods of reading and writing data from/ on semiconductor memory device, and	365/145	365/149
8	<input type="checkbox"/>	<input type="checkbox"/>	US 6387712 B1	20020514	32	Process for preparing ferroelectric thin films	438/3	257/E21.272; 257/E29.164;
9	<input type="checkbox"/>	<input type="checkbox"/>	US 6380573 B1	20020430	34	Semiconductor memory device and method for producing the same	257/295	257/308; 257/309;
10	<input type="checkbox"/>	<input type="checkbox"/>	US 6370056 B1	20020409	14	Ferroelectric memory and method of operating same	365/145	365/185.08
11	<input type="checkbox"/>	<input type="checkbox"/>	US 6356475 B1	20020312	126	Ferroelectric memory and method of reading out data from the ferroelectric	365/145	365/189.01